

Power Electronics

Principles, Evolution and Trends

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College of Engineering Trivandrum

Part - I

Principles

What is Power Electronics?

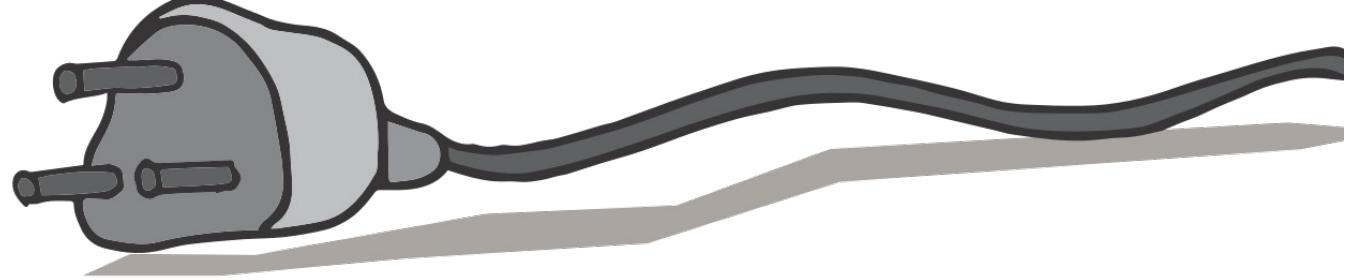
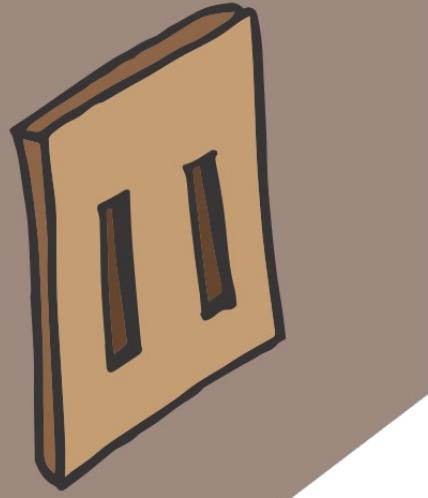
Efficient Conversion,
Conditioning & Control of
Electrical Power

Using Power Semiconductor Devices



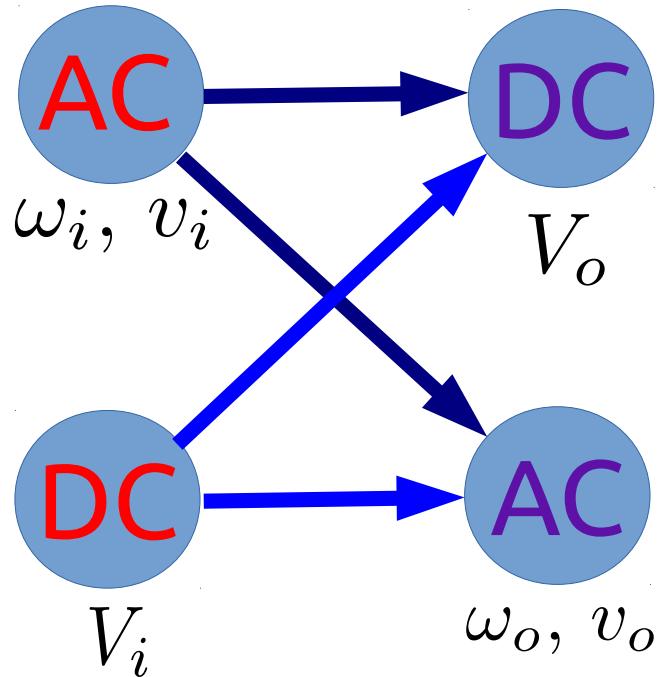
Source: Wikimedia Commons

Why Power Conversion?

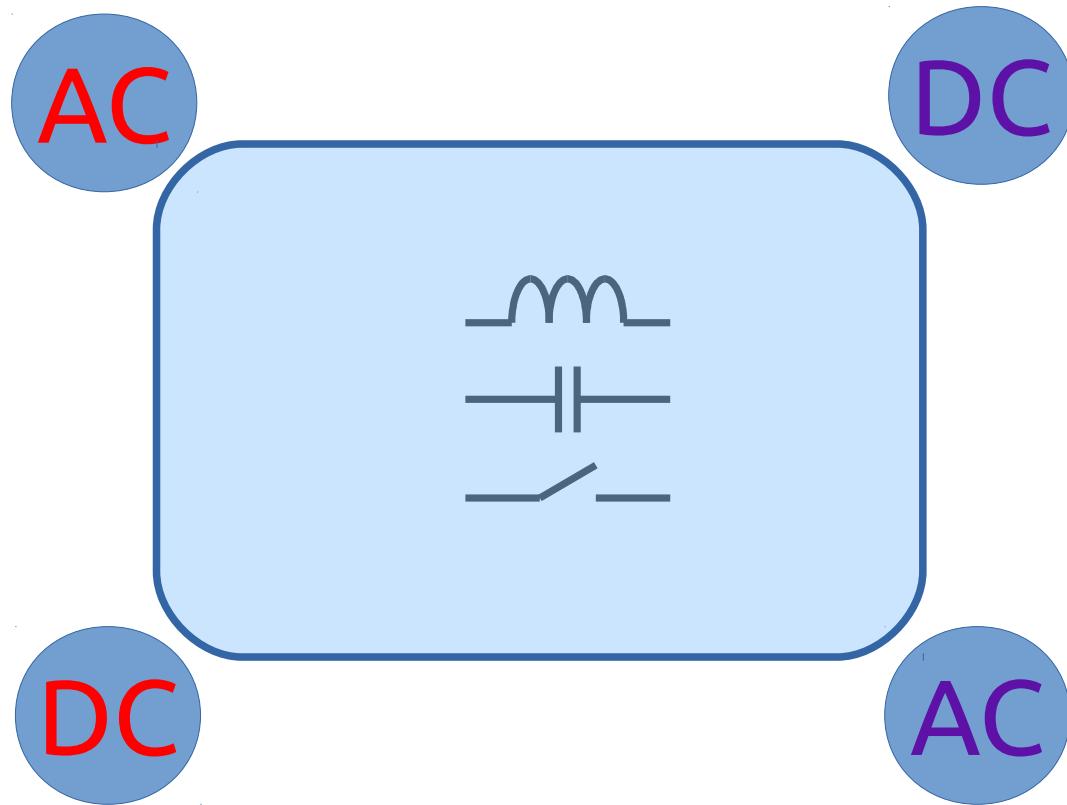


Incompatible
Source and Sink

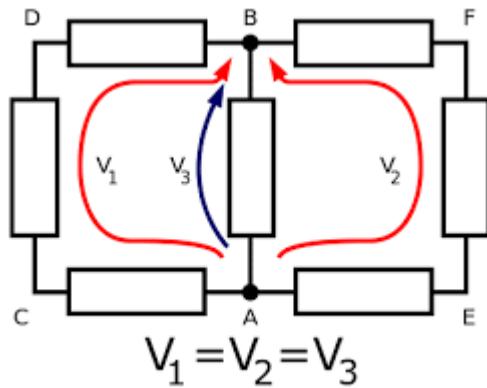
Conversion Functions



The Switch Matrix



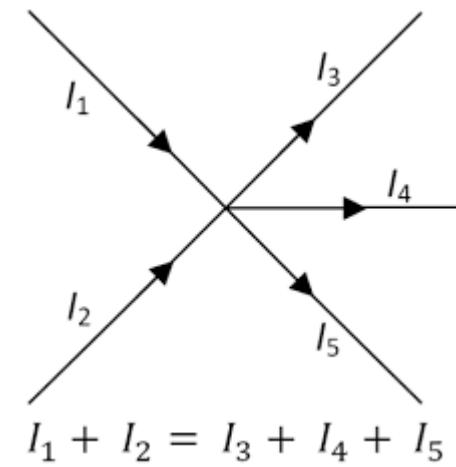
Restrictions



KVL

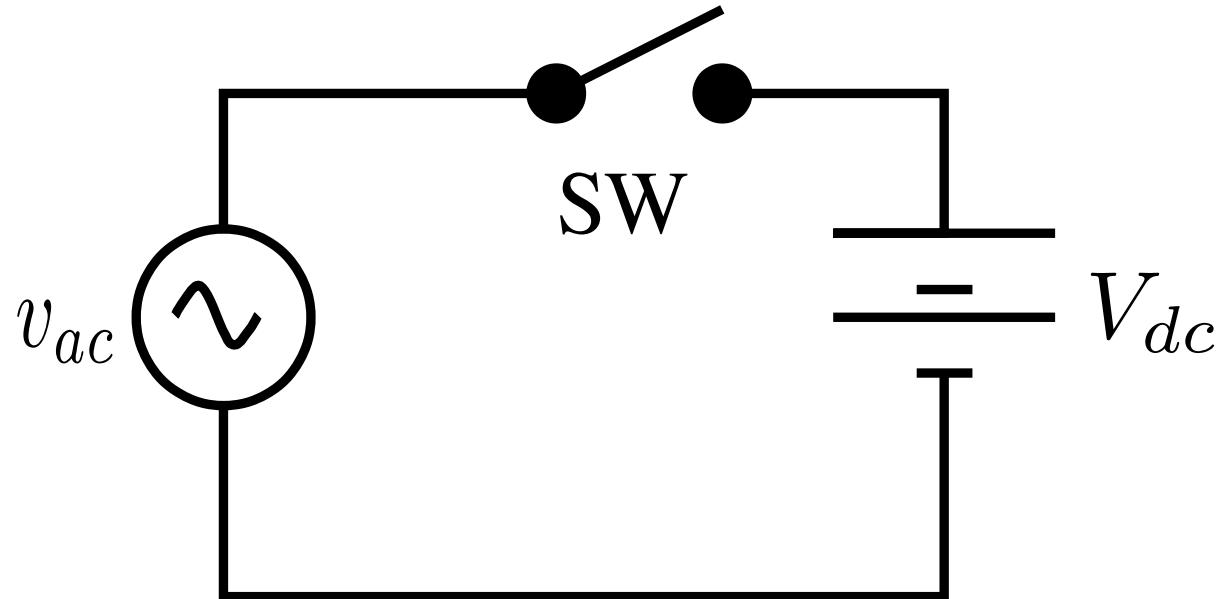


Source: Wikimedia Commons

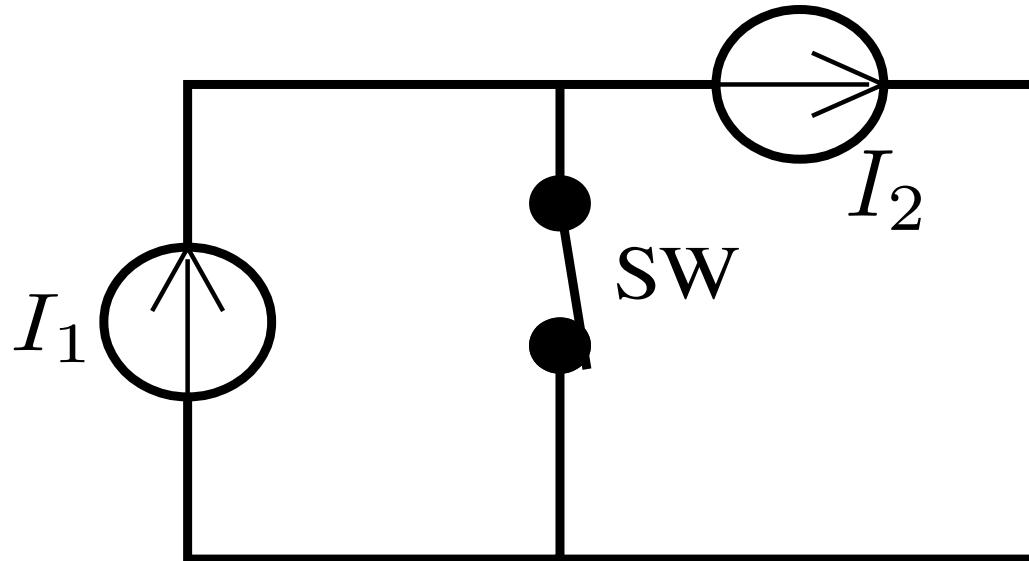


KCL

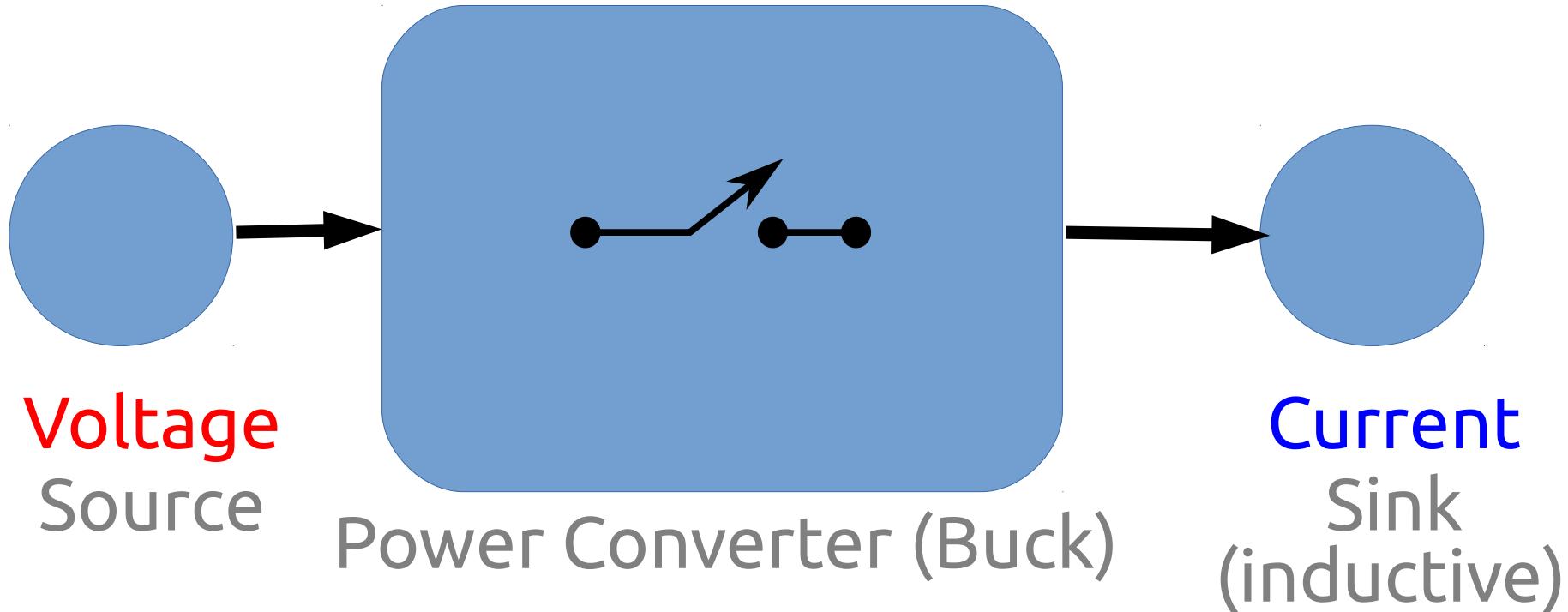
Switch Can't be Closed!



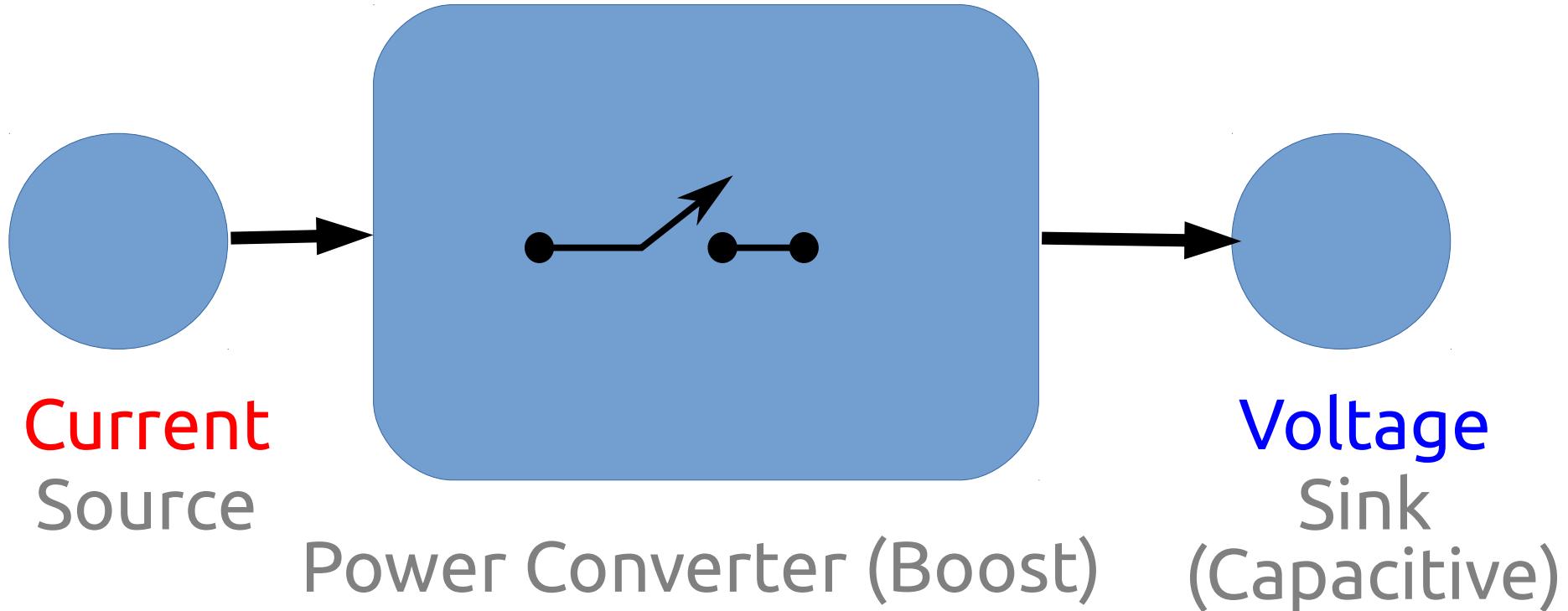
Switch Can't be Opened!



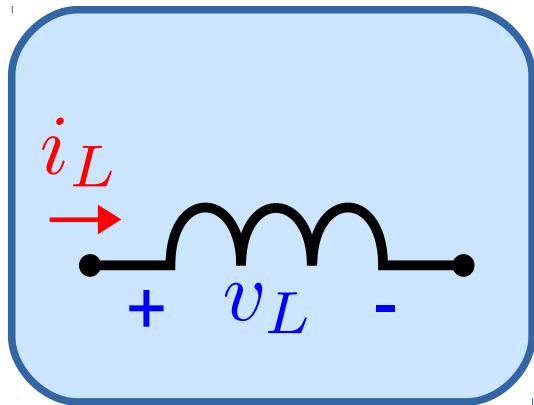
Source Must Be Dual To Sink



Source Must Be Dual To Sink



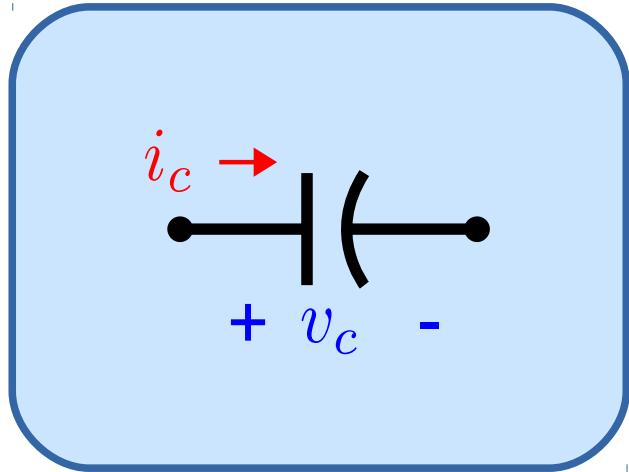
Passive Elements



L: Current-Stiff Element
Can interface two
voltage sources



Passive Elements



C: Voltage-Stiff Element

Can interface two
current sources



Source: Wikimedia Commons

Power Switching Devices



MOSFETs

IGBTs

SCRs

GTOs

IGCTs....

Source: Wikimedia Commons

Part - II

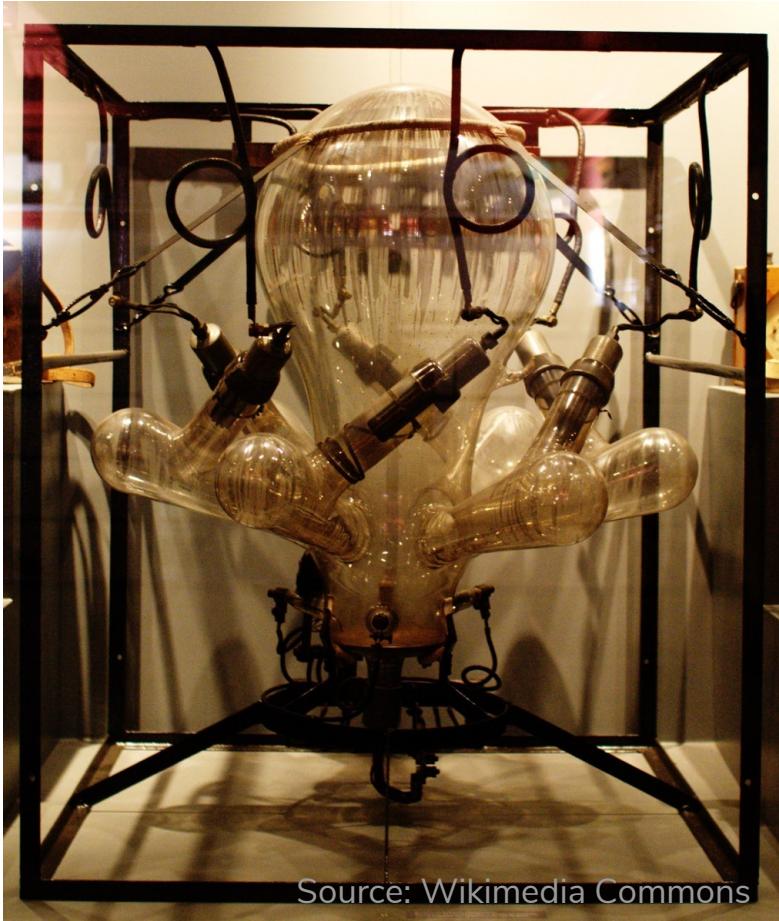
The Evolution

History

1902-1920

Mercury Arc Rectifiers
Thermionic Vacuum Tubes

Triodes/Diodes as **variable resistors**
(gate control)/current Control



History



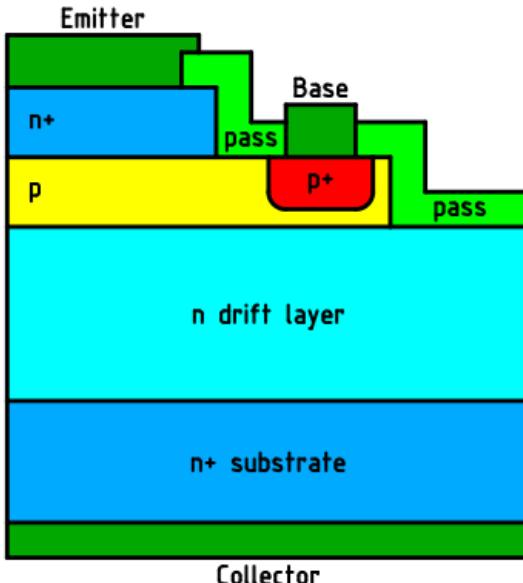
Source: Wikimedia Commons

1925-28:

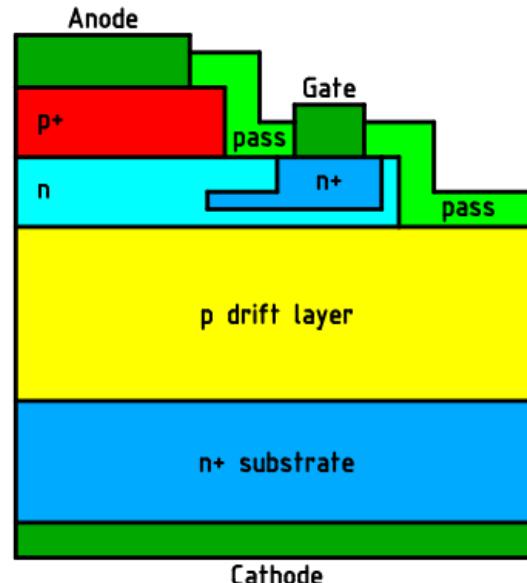
The First “Inverter” using
triodes as **switches**

(D. C. Prince, GE)

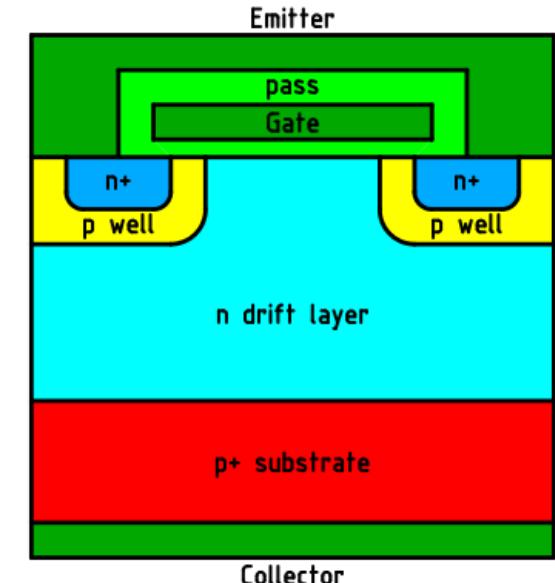
Semiconductor Devices



BJT
1970s



Thyristor
1956



IGBT
1983

Source: Wikimedia Commons

Modern Power Devices



Ruggedness
Controllability

Modern Power Devices

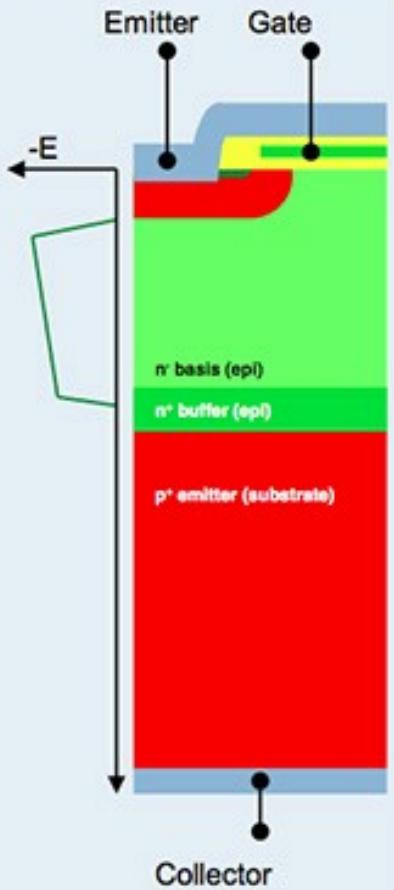
Switching Time
Losses



IGBTs

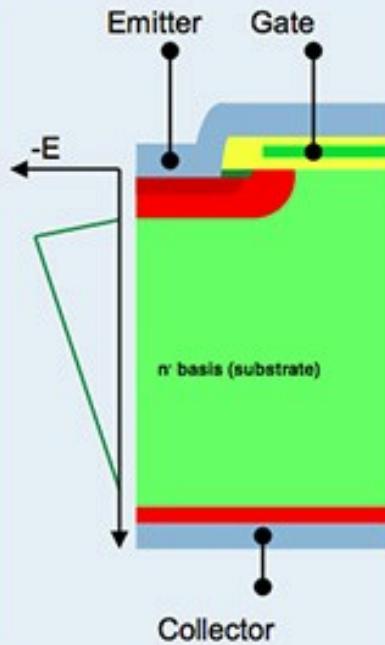
Punch Through

(ROW: 1988)



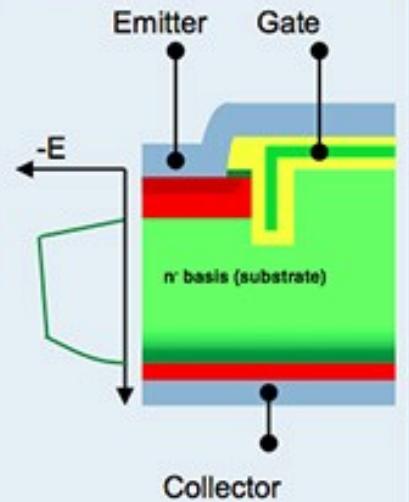
Non Punch Through

(IFX: 1990 ROW:1997)



TRENCHSTOP™

(IFX: 2000 ROW:2006)



Advantages

Implanted Back-Emitter better
adjustable

Performance

Lower Switching losses
Higher Switching Robustness

Advantages

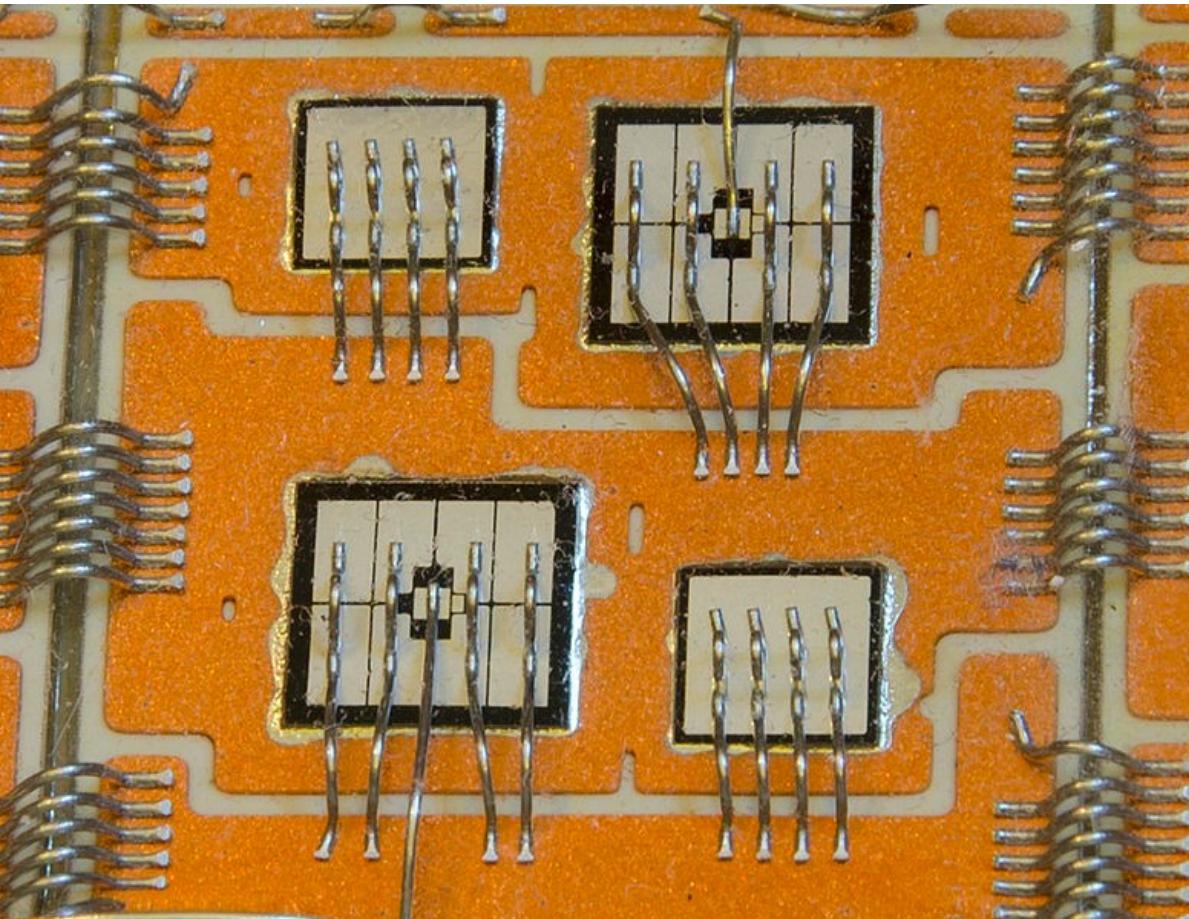
Implanted Back-Emitter
Thinner Base Region

Performance

Lower VCEsat
Lower Switching losses
Robustness like NPT

Source: Digikey/Infineon

Modern IGBTs



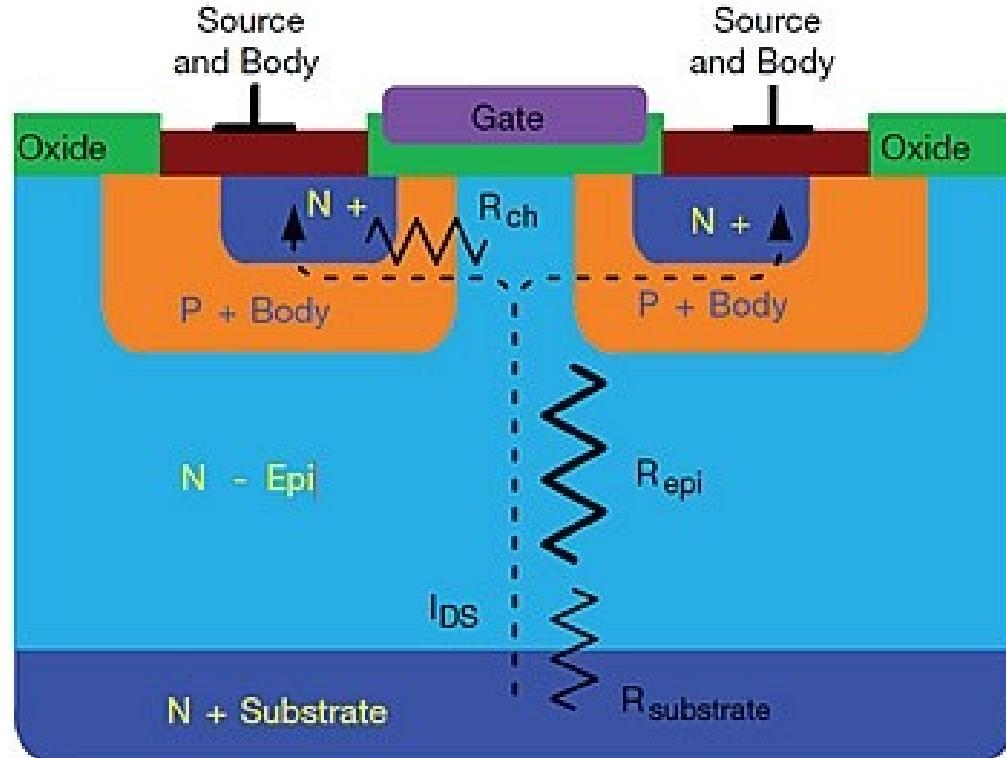
60%
Reduction in V_{CE}

Trench FieldStop

Infineon Module
Source: Wikimedia Commons

MOSFETs

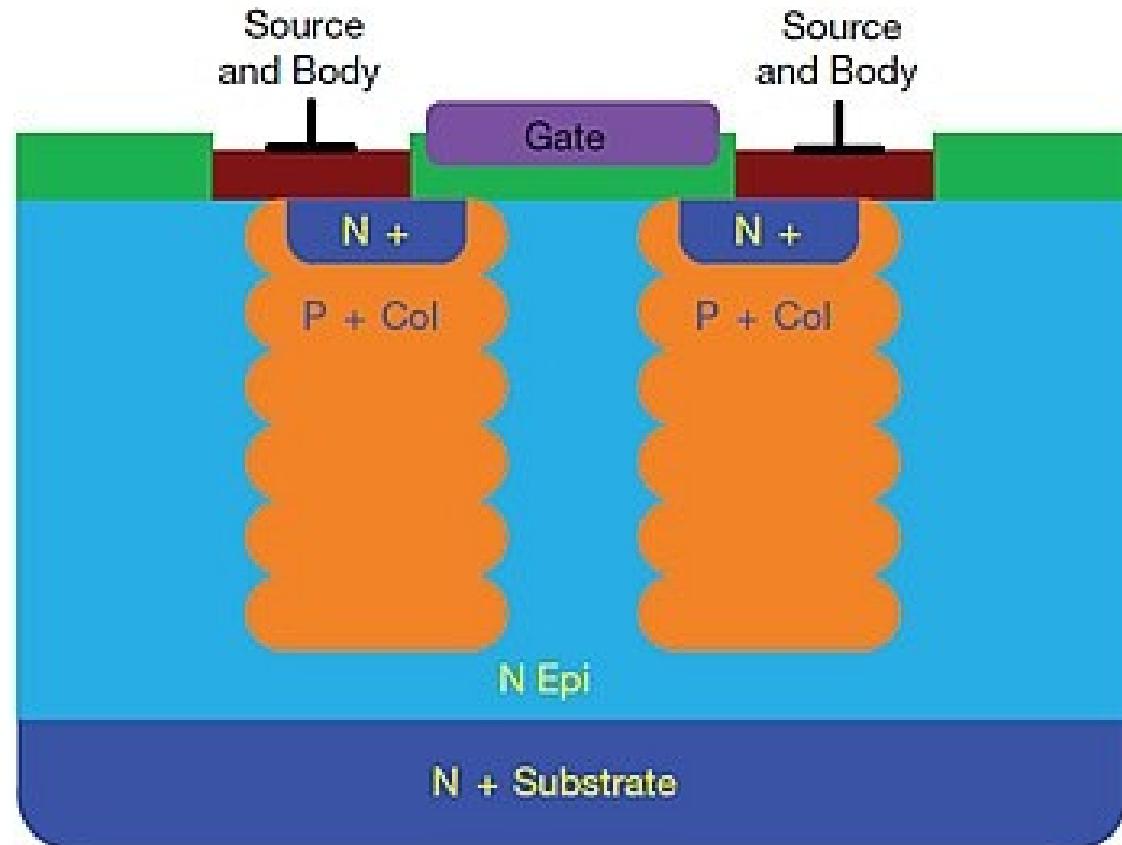
Planar MOSFETs (Conventional)



Source: www.eenewspower.com

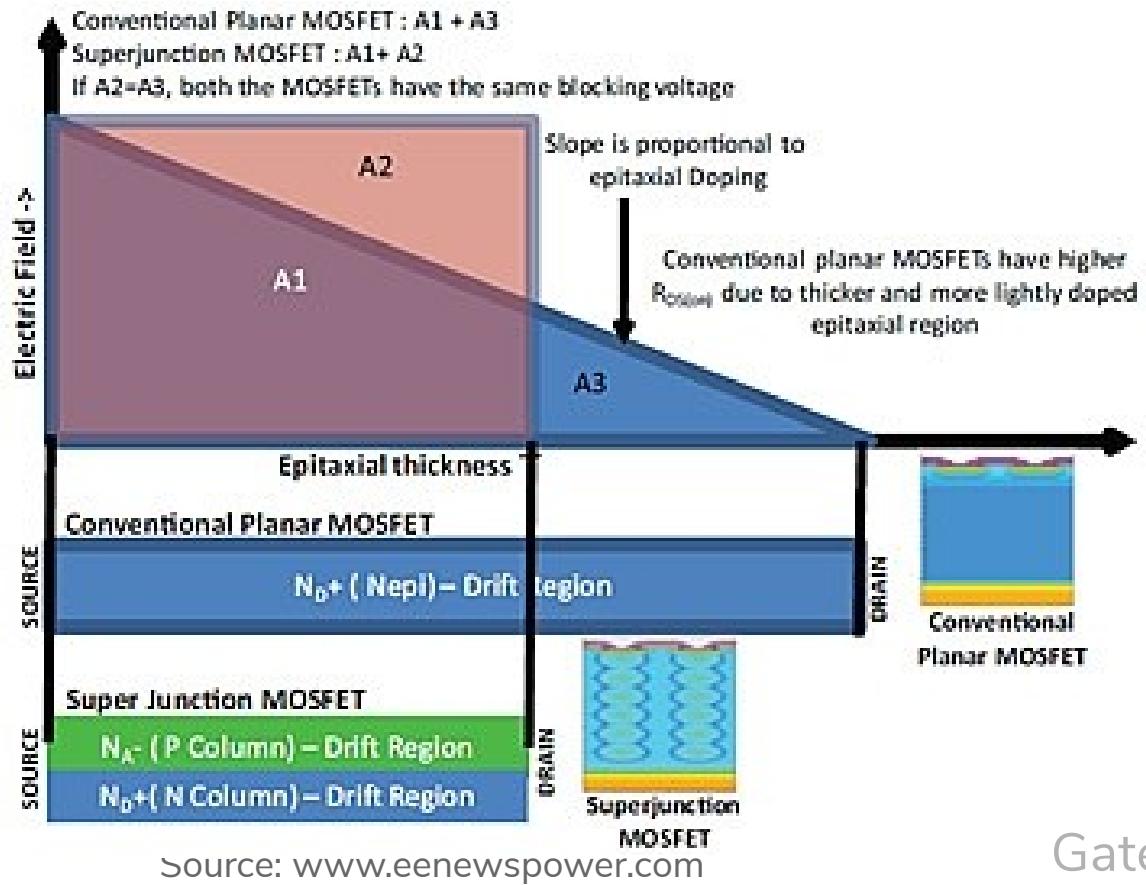
Modern MOSFETs

SuperJunction MOSFETs



Source: www.eenewspower.com

Modern MOSFETs



Up to
50%
Reduction
in $R_{DS(ON)}$
Gate Cap, Output Charge, Die Size

Challenges

- Packaging
 - Wafer Handling
 - Low R_{th}
 - Low L_s

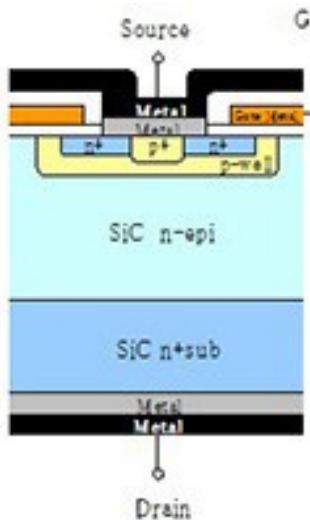
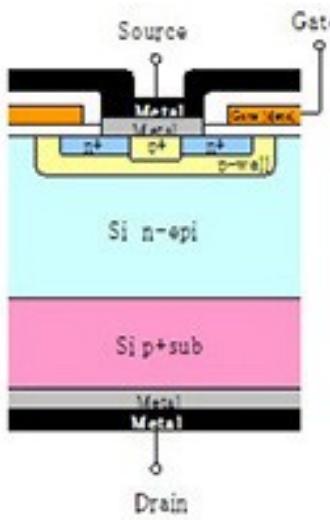
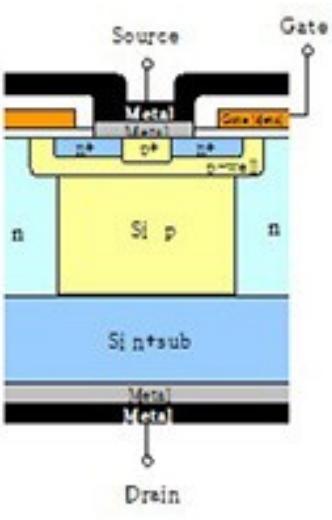
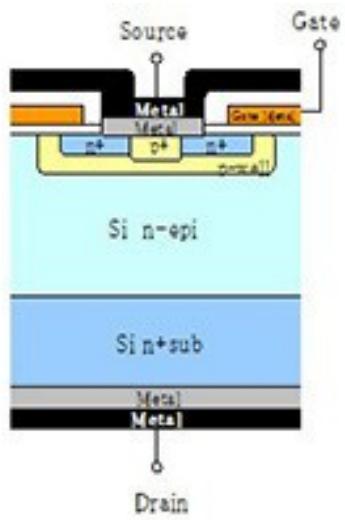
Wide Bandgap Devices

SiC

GaN

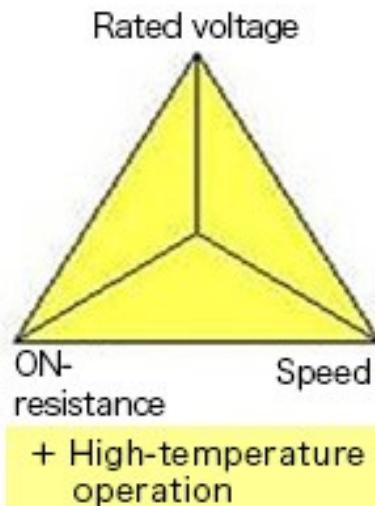
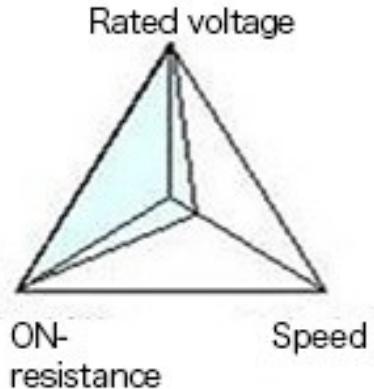
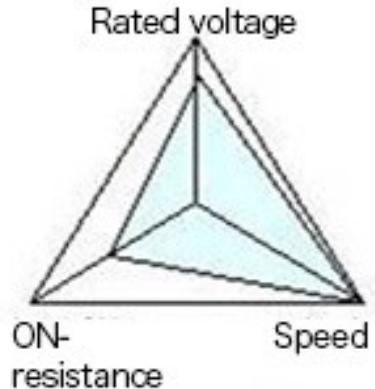
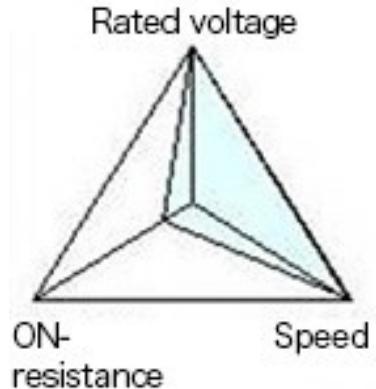
Property	Si	SiC
Band gap energy (eV)	1.12	3.26
Breakdown electric field (V/cm)	2×10^5	2.2×10^6
Thermal conductivity (W/cmK)	1.5	4.56
Maximum junction temperature (°C)	200	600

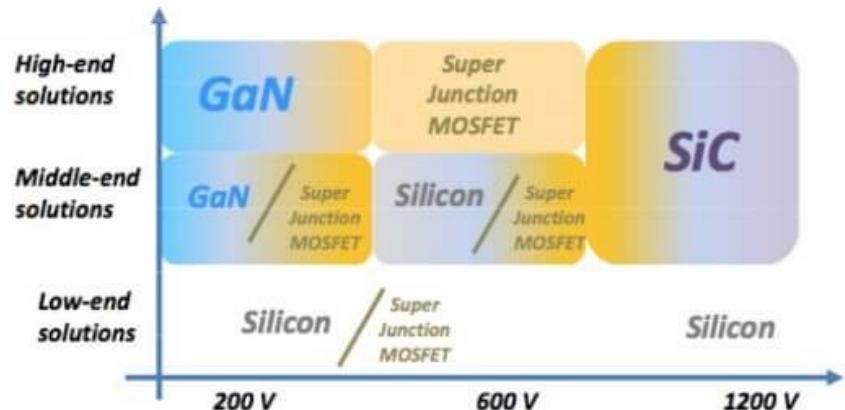
Source: Nagarajan Sridhar, "Power Electronics in Automotive Applications," White Paper, Texas Instruments, 2013



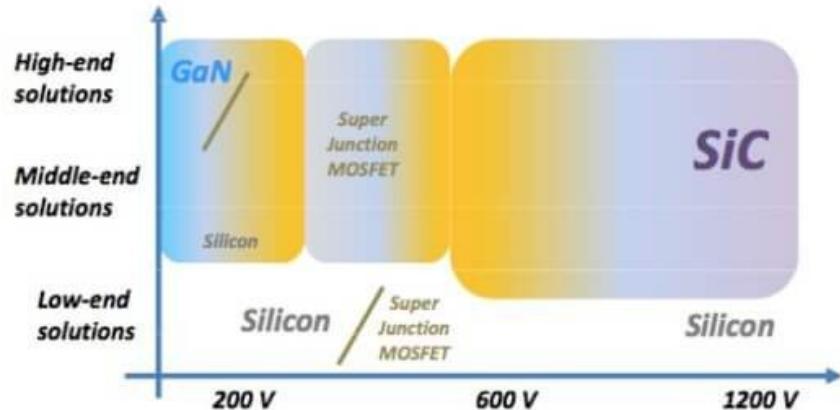
SiC FETs

Source:
micro.rohm.com

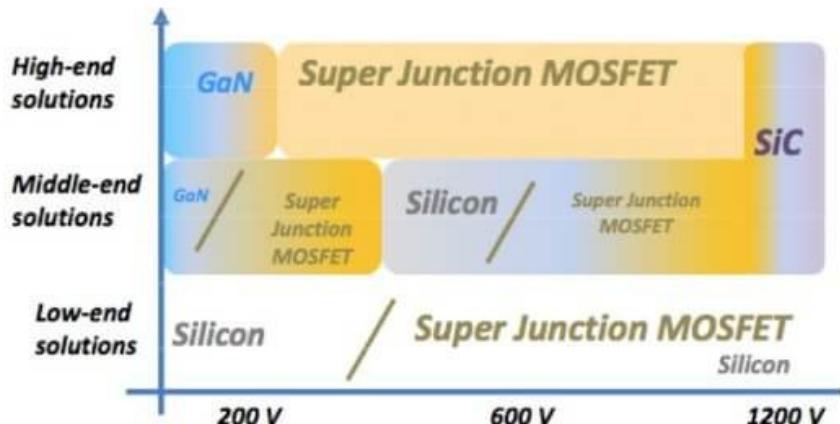




What Yole Developement showed in 2011 as future view



A SiC supplier's view of future



A Super Junction supplier's view of future

Source: www.pntpower.com



Now that 600V GaN-on-Si is qualified, a GaN solution supplier's view for future

The Old Question

MOSFETs Or IGBT?

Voltage Rating >1700V, <400V

Switching Frequency kHz, MHz?

The New Question

SiC Or GaN?

MOSFETs or IGBTs?

Control/Modulation

Mature

- PWM

- Predictive

Some Future Directions

- Heuristics based

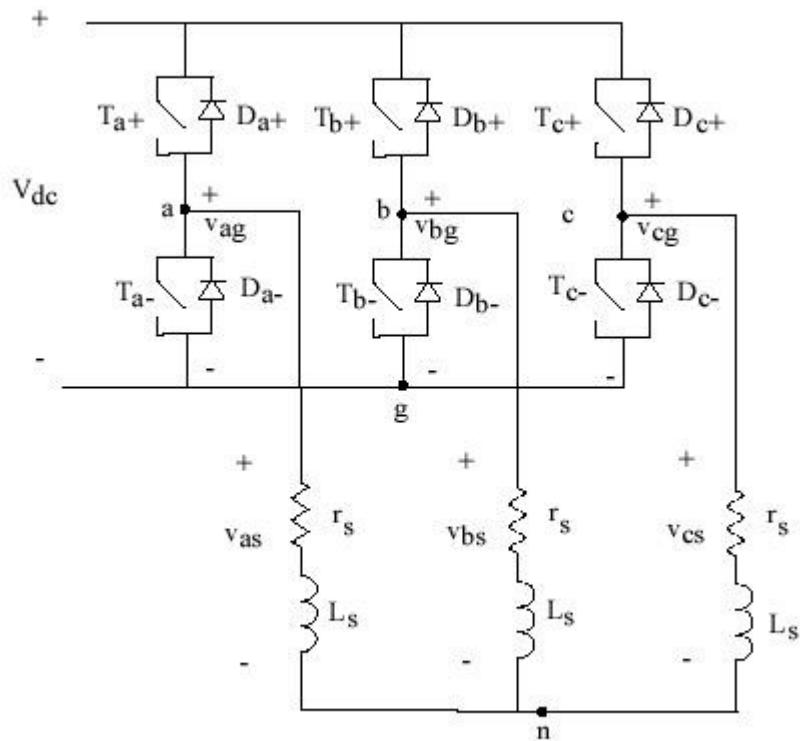
- Model Based Control

Future Trends



What remains the same?

Topologies



Source: Wikimedia Commons

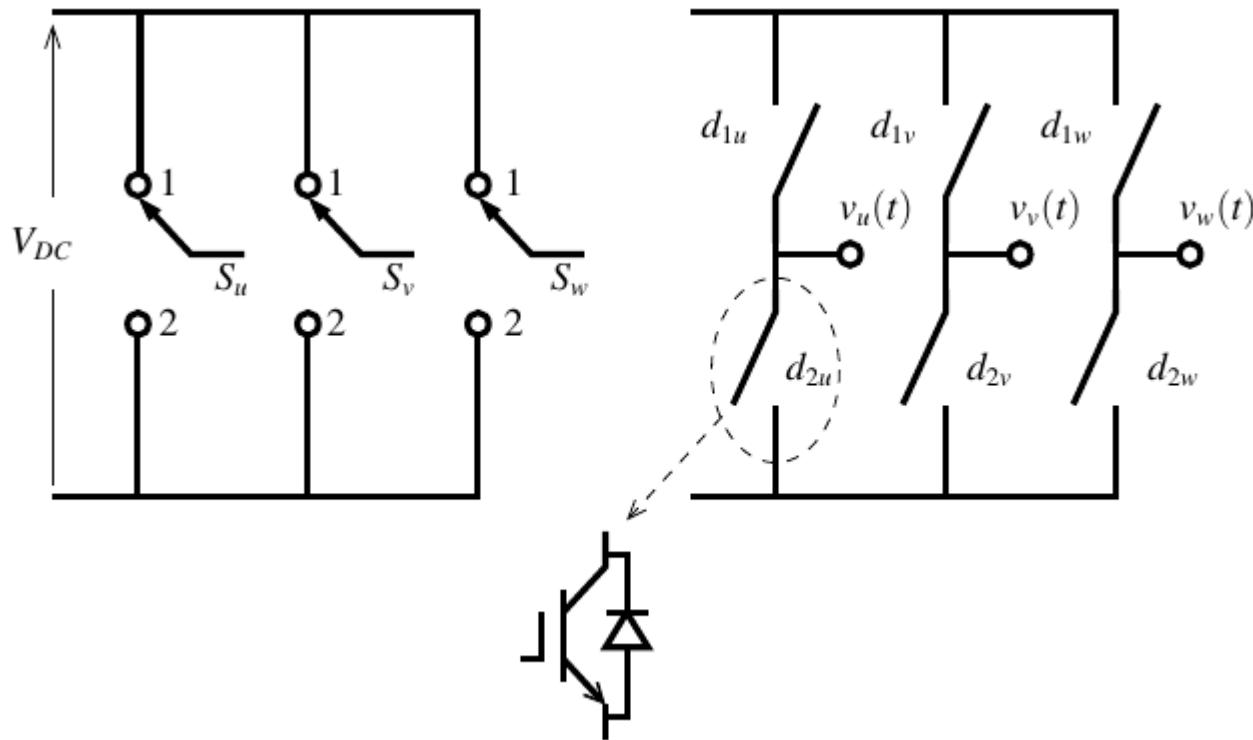
Major Topologies

- Bridge (2-Level, 3-Level)
- Interleaved Topologies
- Soft-switching (ZVT - LLC)
- Isolated Low Power Topologies
- Dual-Active Bridge (DAB)
- Current-Fed Dual Topologies

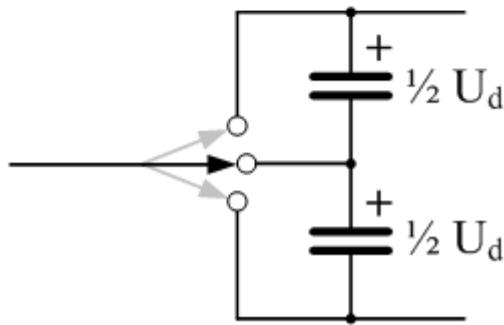
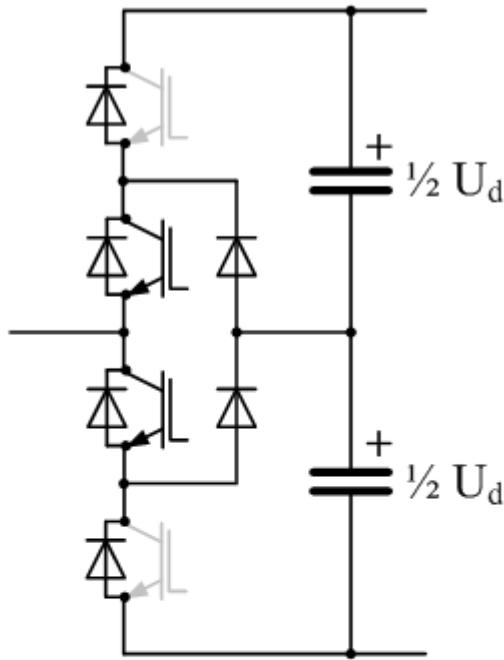
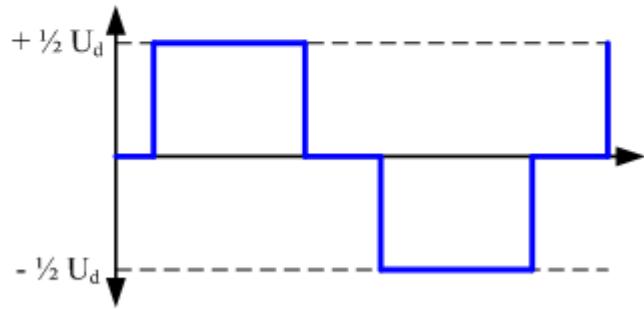
Architectures!



Bridge

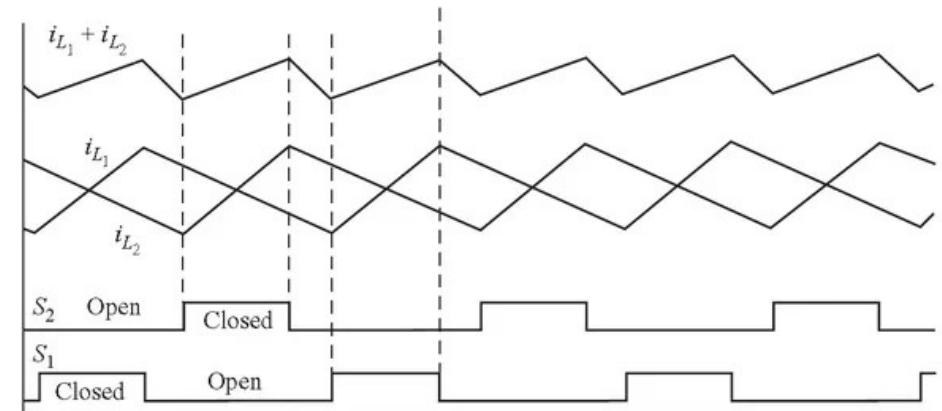
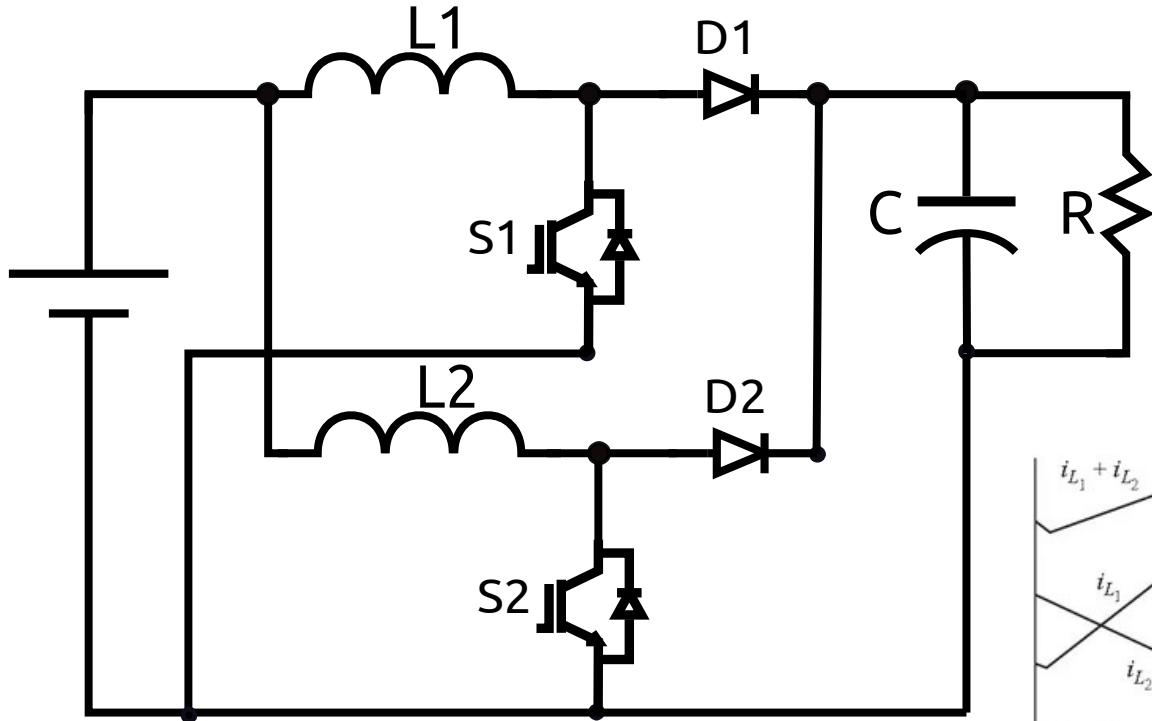


3-Level



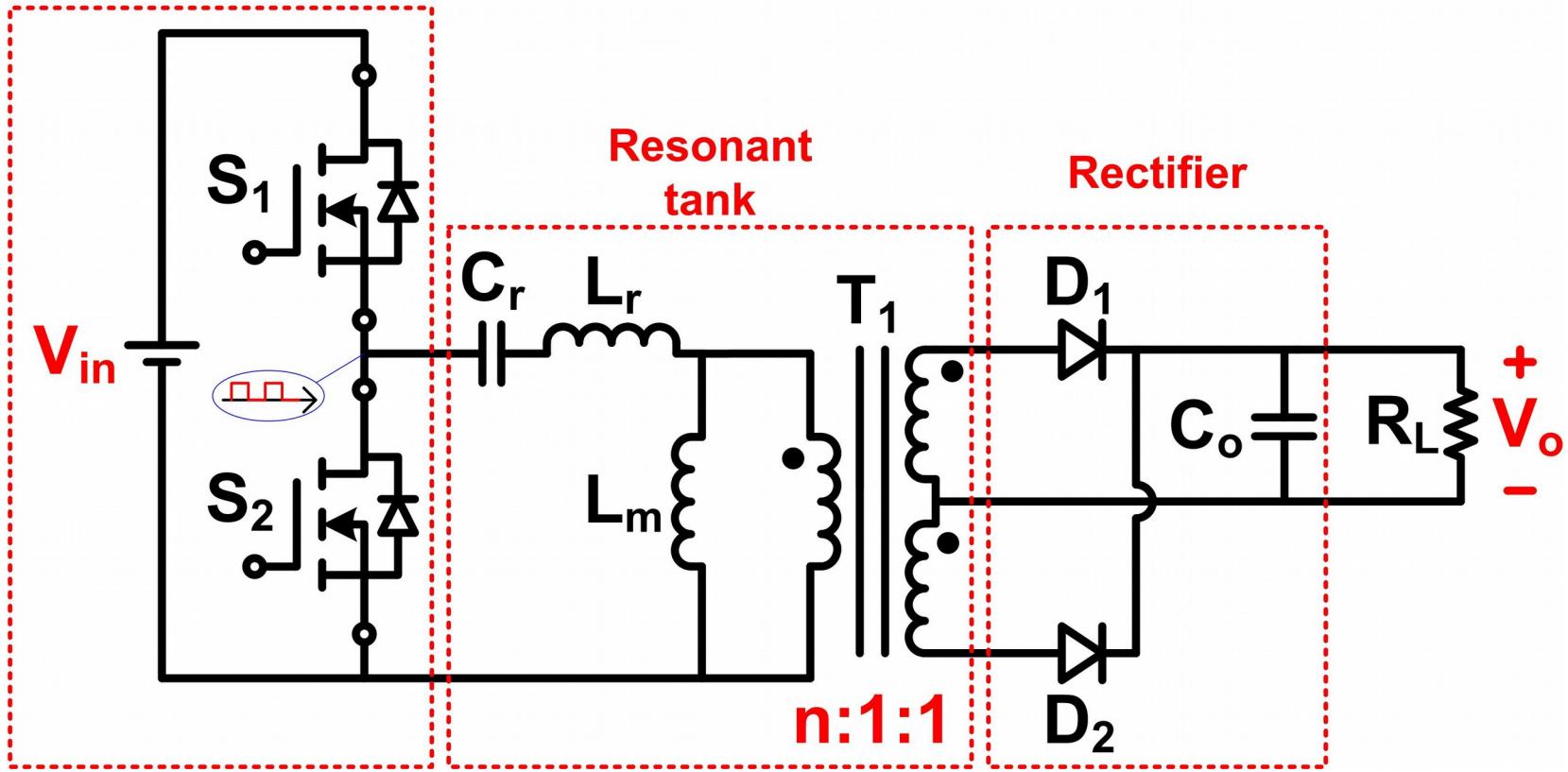
Source: Wikimedia Commons

Interleaved Boost

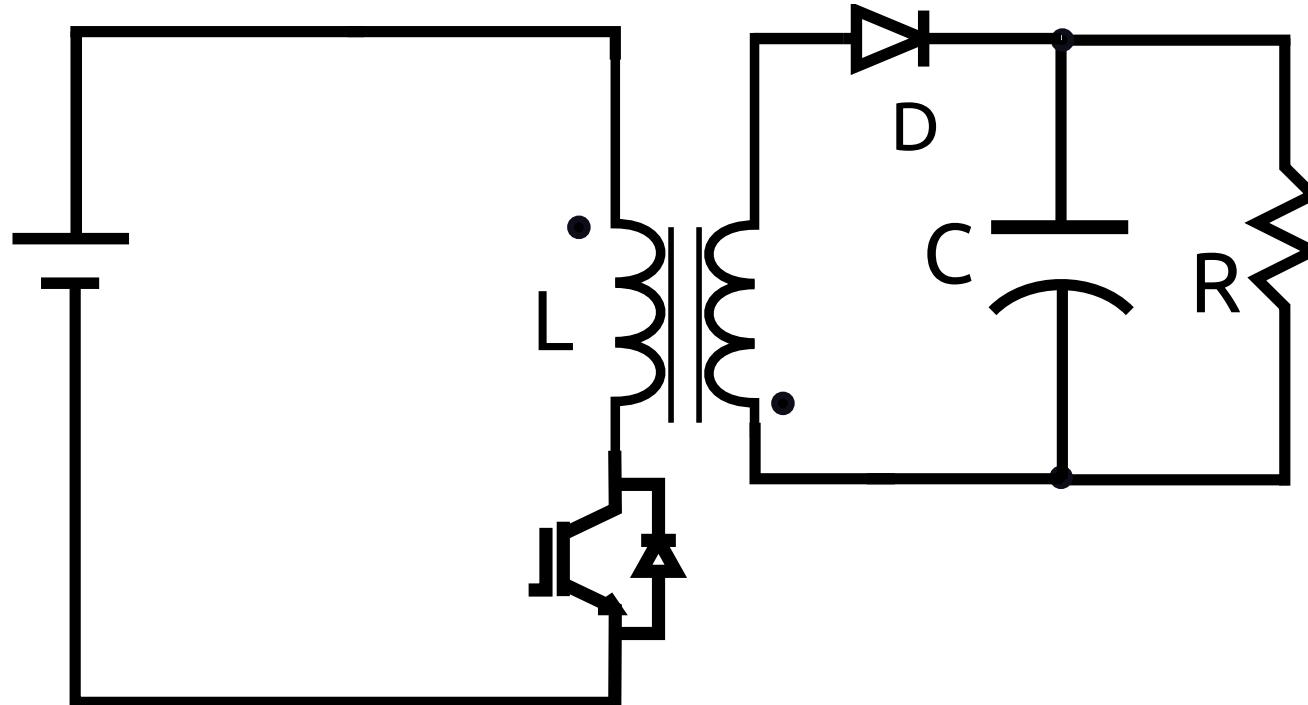


LLC Converters

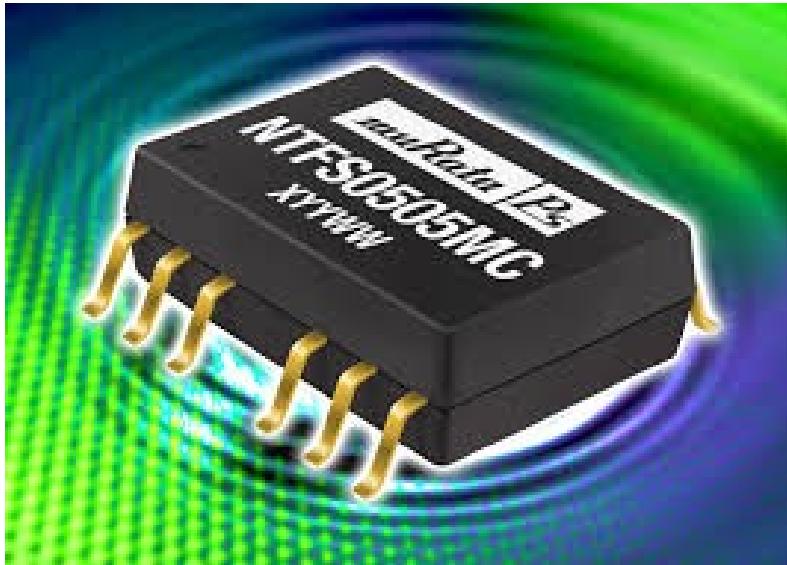
Switching Network



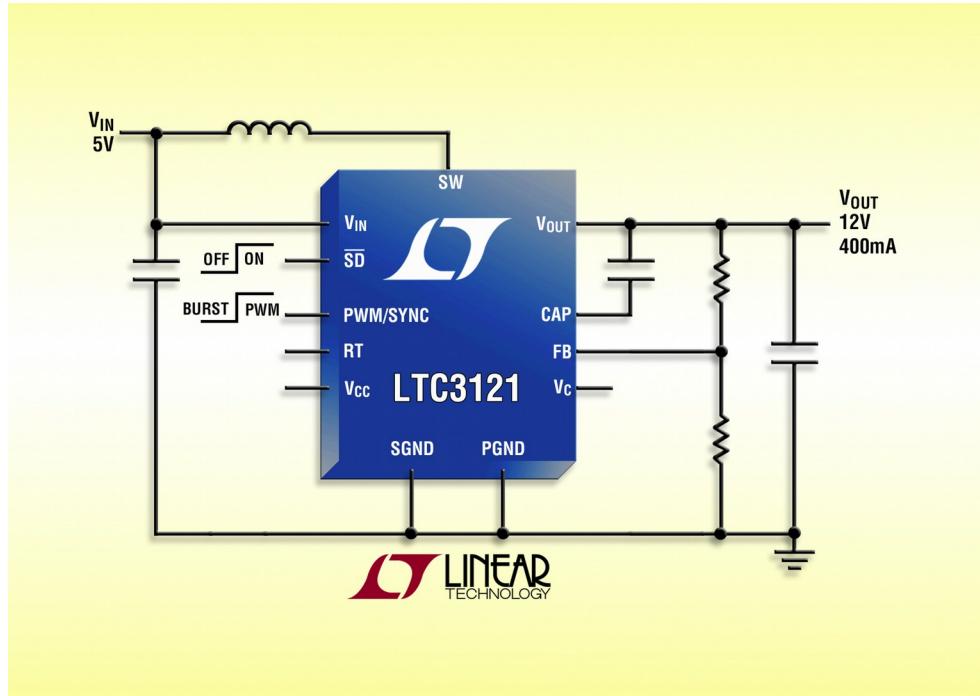
Isolated Low Power Converters



Integrated Low-Power DC-DC Converters

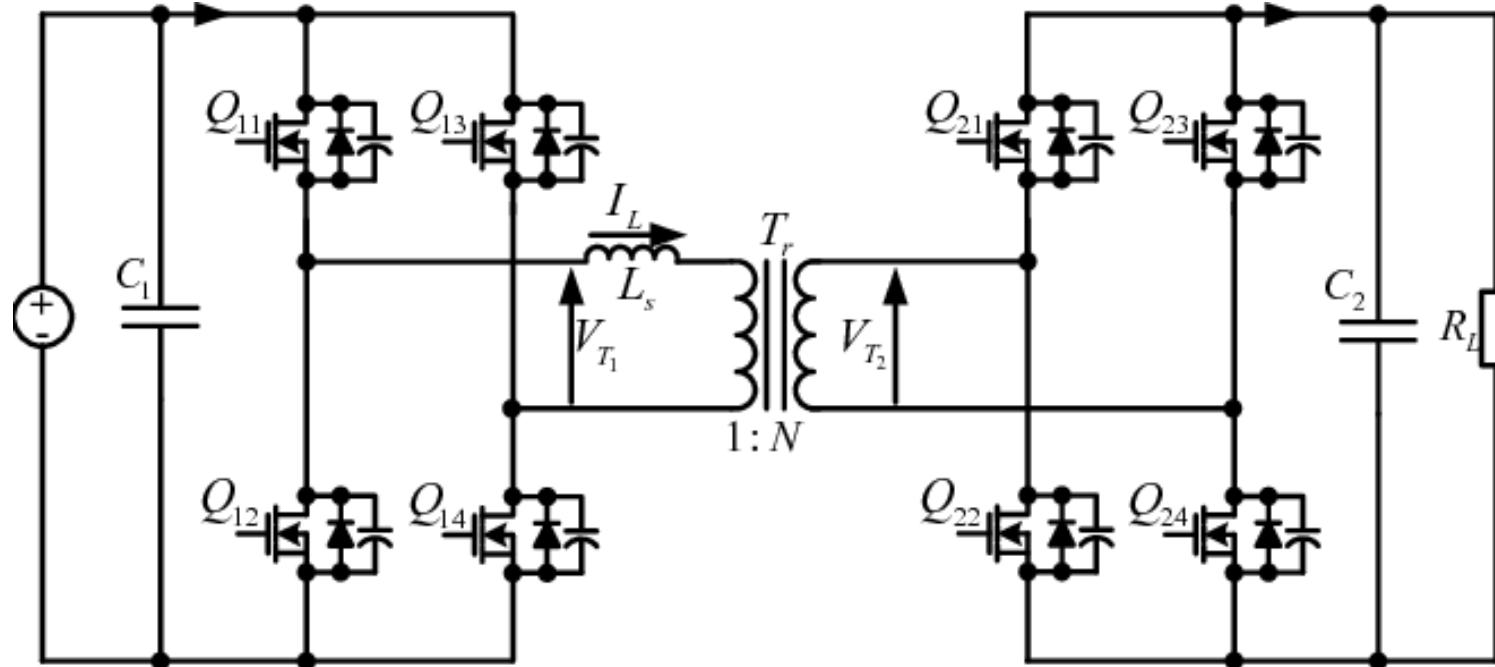


Source: Murata Power Solutions



Source: Linear Technology (Now Analog Corp)

Isolated High Power Converters



Source: researchgate.net

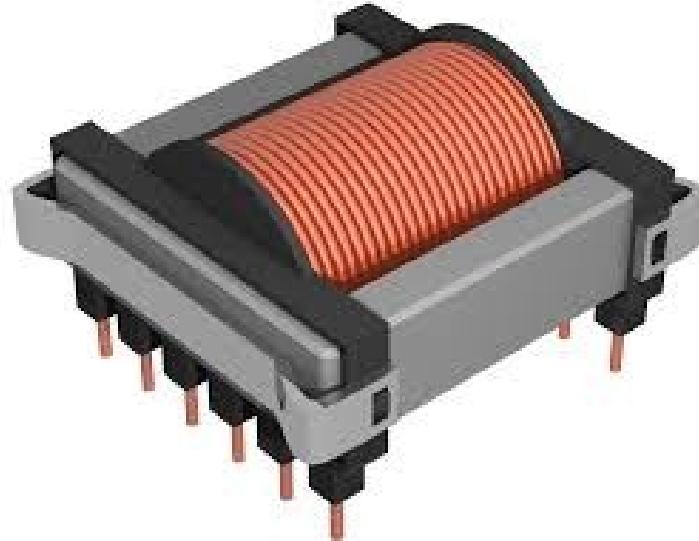
Dual Active Bridge

What remains the same?

Magnetics

Materials

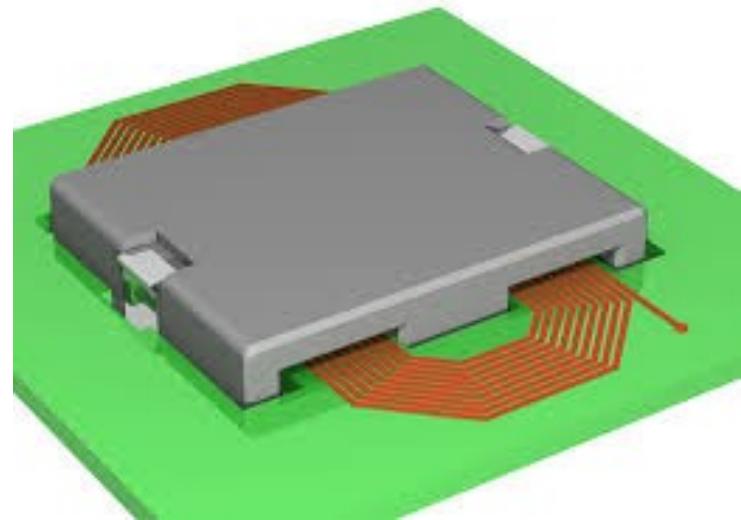
Limitations



Source: Wikimedia Commons

Some Modern Trends

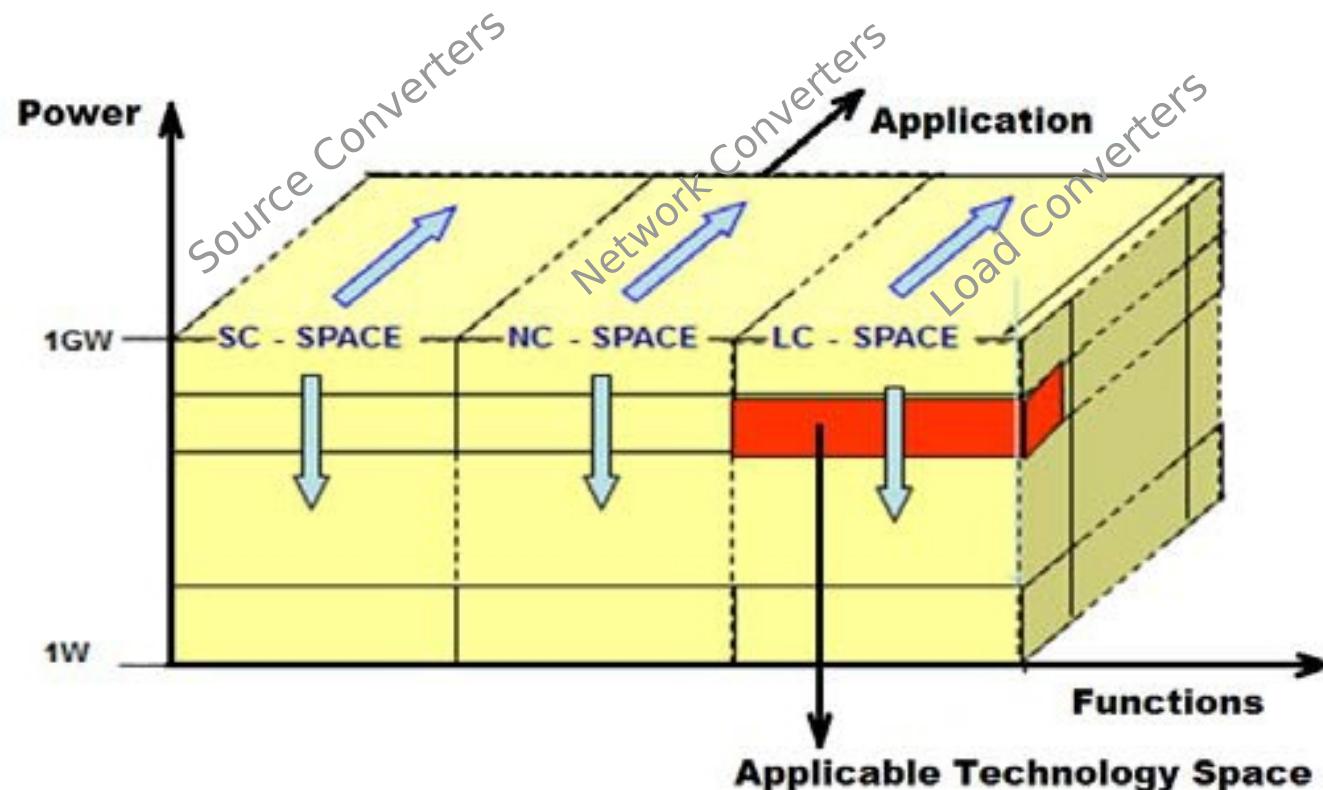
Geometry:
Planar, PCB



Source: Wikimedia Commons

Application Areas

“Technology Space” in PE



Source: J. D. van Wyk & F. C. Lee, "On a Future for Power Electronics", IEEE Journal of Emerging and Selected Topics in PE, Vol. 1, No. 2, June 2013

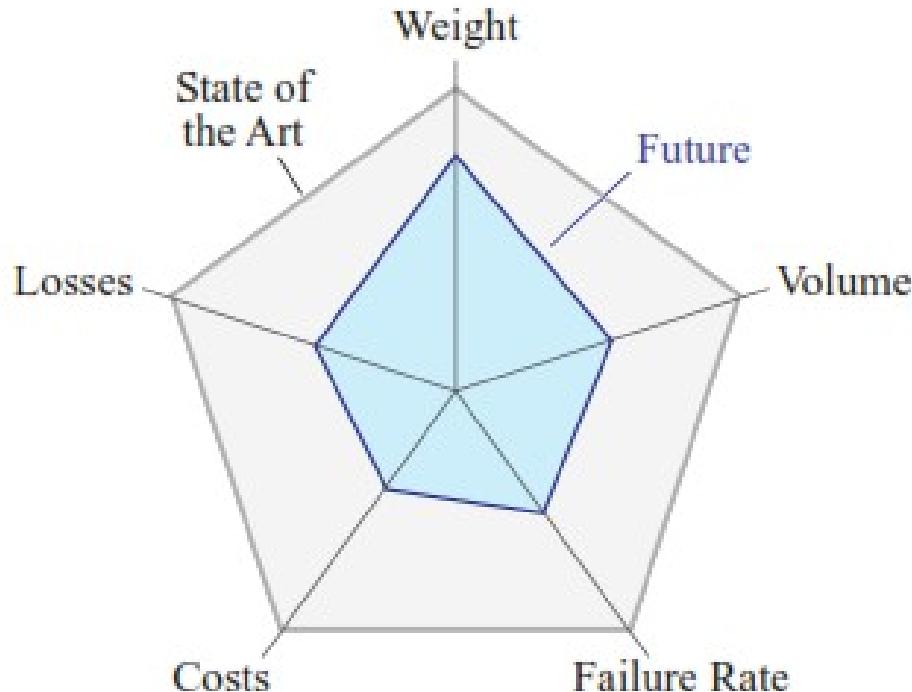
New Areas

- Smart Grid: Evolution of Power Grid
- Distributed Power Systems
- Transportation: EVs, HEVs, More
Electric Aircrafts, Ships.

Electric Vehicles

- Regenerative braking (AC/DC)
- On-board charger (AC/DC)
- Dual-battery system (DC/DC)
- Battery management for Lithium-Ion (Li-Ion) batteries
- 48V-12V bi-directional power supply
- 400V Battery Systems
- Bi-directional 400V-12V power supply (DC/DC)
- Traction motor (DC/AC)

New Targets



Source: J. W. Kolar et. al, "Performance Trends and Limitations of Power Electronic Systems"

New Targets



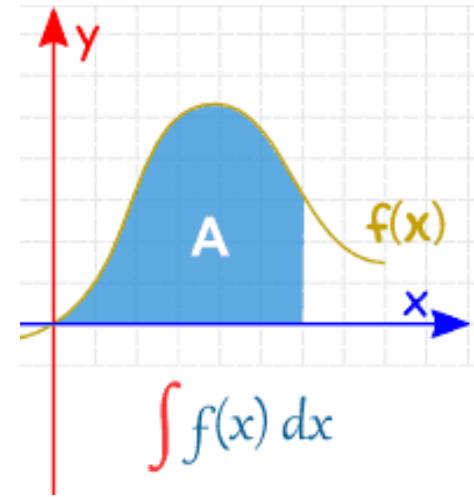
Source: www.infineon.com/power

New Targets

- Power Density
- Efficiency
- Costs

New Paradigms

- Power Conversion -> Energy Management
- Converters -> “Systems”
- Life Cycle Costs



Source: mathisfun.com

Summary

- Trends in a mature field influenced by external factors
- More emphasis on system level design and optimization

References

1. Jose I. Leon, *et. al.*, "The Essential Role and the Continuous Evolution of Modulation Techniques for Voltage-Source Inverters in the Past, Present, and Future Power Electronics," IEEE TRANSACTIONS ON INDUSTRIAL ELECTRONICS, VOL. 63, NO. 5, MAY 2016
2. KAWANO Masashi, HIROSE Jun And AIHARA Takashi, "Power Electronics Technology: Current Status and Future Outlook," Fuji Electric
3. Hubert Kerstin, Björn Rentemeister, Thomas Risse, "Where is the Journey Headed? : The Future of High-Power Semiconductors," Bodo's Power Systems, November 2014, [Obtained from www.infineon.com/power]

References

4. J. W. Kolar, J. Biela, S. Waffler, T. Friedli, and U. Badstuebner, "Performance trends and limitations in power electronics," in Proc. 6th Int. CIPS, Mar. 2010, pp. 17–36.
5. J. D. van Wyk & F. C. Lee, "On a Future for Power Electronics", IEEE Journal of Emerging and Selected Topics in PE, Vol. 1, No. 2, June 2013
6. S. S. Williamson, A. K. Rathore and F. Musavi, "Industrial Electronics for Electric Transportation: Current State-of-the-Art and Future Challenges," in IEEE Transactions on Industrial Electronics, vol. 62, no. 5, pp. 3021-3032, May 2015. doi: 10.1109/TIE.2015.2409052

References

7. www.eenewspower.com
8. Industry Sources: Web sites of Infineon, Onsemi, Rhom, Mitsubishi Electric, IRF, Toshiba, etc.

Thank You